

# DATA SHEET

## **PMBFJ174 to 177** P-channel silicon field-effect transistors

Product specification  
File under Discrete Semiconductors, SC07

April 1995

**P-channel silicon field-effect transistors**

**PMBFJ174 to 177**

**DESCRIPTION**

Silicon symmetrical p-channel junction FETs in plastic microminiature SOT23 envelopes. They are intended for application with analogue switches, choppers, commutators etc. using SMD technology. A special feature is the interchangeability of the drain and source connections.

**PINNING**

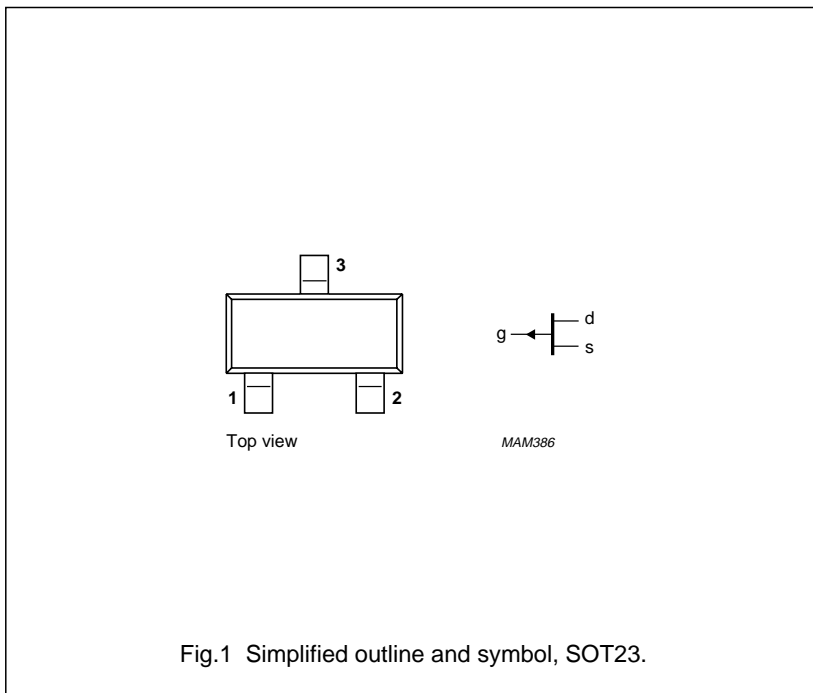
- 1 = drain
- 2 = source
- 3 = gate

**Note**

- 1. Drain and source are interchangeable.

**Marking codes:**

- 174 : p6X
- 175 : p6W
- 176 : p6S
- 177 : p6Y



**QUICK REFERENCE DATA**

|   |              |      |                 |            |            |              |
|---|--------------|------|-----------------|------------|------------|--------------|
| Drain-source voltage  | $\pm V_{DS}$ | max. | 30              | V          |            |              |
| Gate-source voltage   | $V_{GSO}$    | max. | 30              | V          |            |              |
| Gate current  | $-I_G$       | max. | 50              | mA         |            |              |
| Total power dissipation<br>up to $T_{amb} = 25^\circ C$     | $P_{tot}$    | max. | 300             | mW         |            |              |
| Drain current<br>$-V_{DS} = 15 V; V_{GS} = 0$               | $-I_{DSS}$   |      | <b>PMBFJ174</b> | <b>175</b> | <b>176</b> | <b>177</b>   |
|   |              | >    | 20              | 7          | 2          | 1,5 mA       |
|   |              | <    | 135             | 70         | 35         | 20 mA        |
| Drain-source ON-resistance<br>$-V_{DS} = 0,1 V; V_{GS} = 0$ | $R_{DS\ on}$ | <    | 85              | 125        | 250        | 300 $\Omega$ |

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**RATINGS**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

|   |              |      |              |                  |
|---|--------------|------|--------------|------------------|
| Drain-source voltage  | $\pm V_{DS}$ | max. | 30           | V                |
| Gate-source voltage   | $V_{GSO}$    | max. | 30           | V                |
| Gate-drain voltage  | $V_{GDO}$    | max. | 30           | V                |
| Gate current (d.c.)   | $-I_G$       | max. | 50           | mA               |
| Total power dissipation<br>up to $T_{amb} = 25\text{ }^\circ\text{C}^{(1)}$ | $P_{tot}$    | max. | 300          | mW               |
| Storage temperature range   | $T_{stg}$    |      | -65 to + 150 | $^\circ\text{C}$ |
| Junction temperature  | $T_j$        | max. | 150          | $^\circ\text{C}$ |

**THERMAL RESISTANCE**

|                                      |               |   |     |     |
|--------------------------------------|---------------|---|-----|-----|
| From junction to ambient in free air | $R_{th\ j-a}$ | = | 430 | K/W |
|--------------------------------------|---------------|---|-----|-----|

**STATIC CHARACTERISTICS** $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

|   |               |   | <b>PMBFJ174</b> | <b>175</b> | <b>176</b> | <b>177</b> |          |
|---|---------------|---|-----------------|------------|------------|------------|----------|
| Gate cut-off current<br>$V_{GS} = 20\text{ V}; V_{DS} = 0$                  | $I_{GSS}$     | < | 1               | 1          | 1          | 1          | nA       |
| Drain cut-off current<br>$-V_{DS} = 15\text{ V}; V_{GS} = 10\text{ V}$      | $-I_{DSX}$    | < | 1               | 1          | 1          | 1          | nA       |
| Drain current<br>$-V_{DS} = 15\text{ V}; V_{GS} = 0$                        | $-I_{DSS}$    | > | 20              | 7          | 2          | 1,5        | mA       |
|   |               | < | 135             | 70         | 35         | 20         | mA       |
| Gate-source breakdown voltage<br>$I_G = 1\text{ }\mu\text{A}; V_{DS} = 0$   | $V_{(BR)GSS}$ | > | 30              | 30         | 30         | 30         | V        |
| Gate-source cut-off voltage<br>$-I_D = 10\text{ nA}; V_{DS} = -15\text{ V}$ | $V_{GS\ off}$ | > | 5               | 3          | 1          | 0,8        | V        |
|   |               | < | 10              | 6          | 4          | 2,25       | V        |
| Drain-source ON-resistance<br>$-V_{DS} = 0,1\text{ V}; V_{GS} = 0$          | $R_{DS\ on}$  | < | 85              | 125        | 250        | 300        | $\Omega$ |

**Note**

1. Mounted on a ceramic substrate of  $8\text{ mm} \times 10\text{ mm} \times 0,7\text{ mm}$ .

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**DYNAMIC CHARACTERISTICS**

$T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

Input capacitance,  $f = 1\text{ MHz}$

$V_{GS} = 10\text{ V}; V_{DS} = 0\text{ V}$

$V_{GS} = V_{DS} = 0$

Feedback capacitance,  $f = 1\text{ MHz}$

$V_{GS} = 10\text{ V}; V_{DS} = 0\text{ V}$

Switching times (see Fig.2 + 3)

Delay time

Rise time

Turn-on time

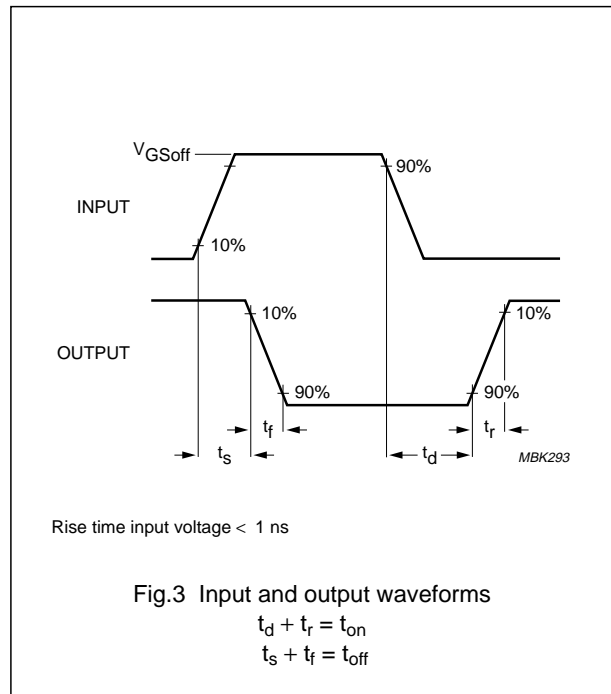
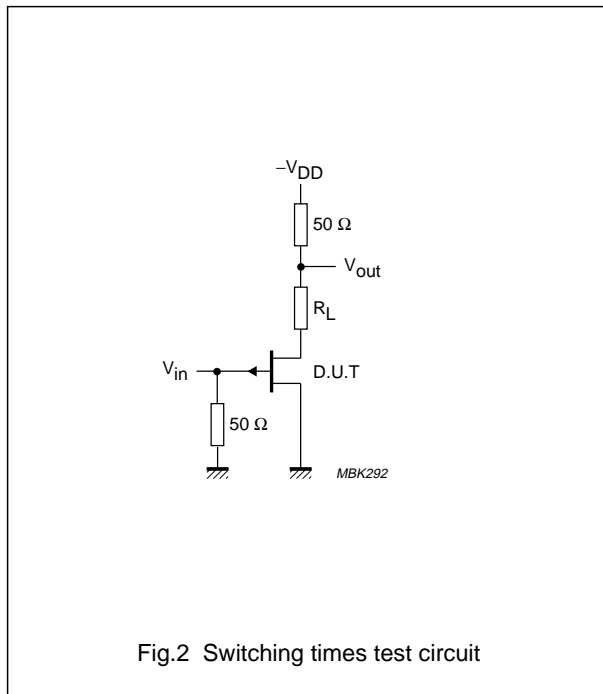
Storage temperature

Fall time

Turn-off time

Test conditions:

|               |      |                 |            |            |               |
|---------------|------|-----------------|------------|------------|---------------|
| $C_{is}$      | typ. | 8               |            |            | pF            |
| $C_{is}$      | typ. | 30              |            |            | pF            |
| $C_{rs}$      | typ. | 4               |            |            | pF            |
|               |      | <b>PMBFJ174</b> | <b>175</b> | <b>176</b> | <b>177</b>    |
| $t_d$         | typ. | 2               | 5          | 15         | 20 ns         |
| $t_r$         | typ. | 5               | 10         | 20         | 25 ns         |
| $t_{on}$      | typ. | 7               | 15         | 35         | 45 ns         |
| $t_s$         | typ. | 5               | 10         | 15         | 20 ns         |
| $t_f$         | typ. | 10              | 20         | 20         | 25 ns         |
| $t_{off}$     | typ. | 15              | 30         | 35         | 45 ns         |
| $-V_{DD}$     |      | 10              | 6          | 6          | 6 V           |
| $V_{GS\ off}$ |      | 12              | 8          | 6          | 3 V           |
| $R_L$         |      | 560             | 1200       | 2000       | 2900 $\Omega$ |
| $V_{GS\ on}$  |      | 0               | 0          | 0          | 0 V           |



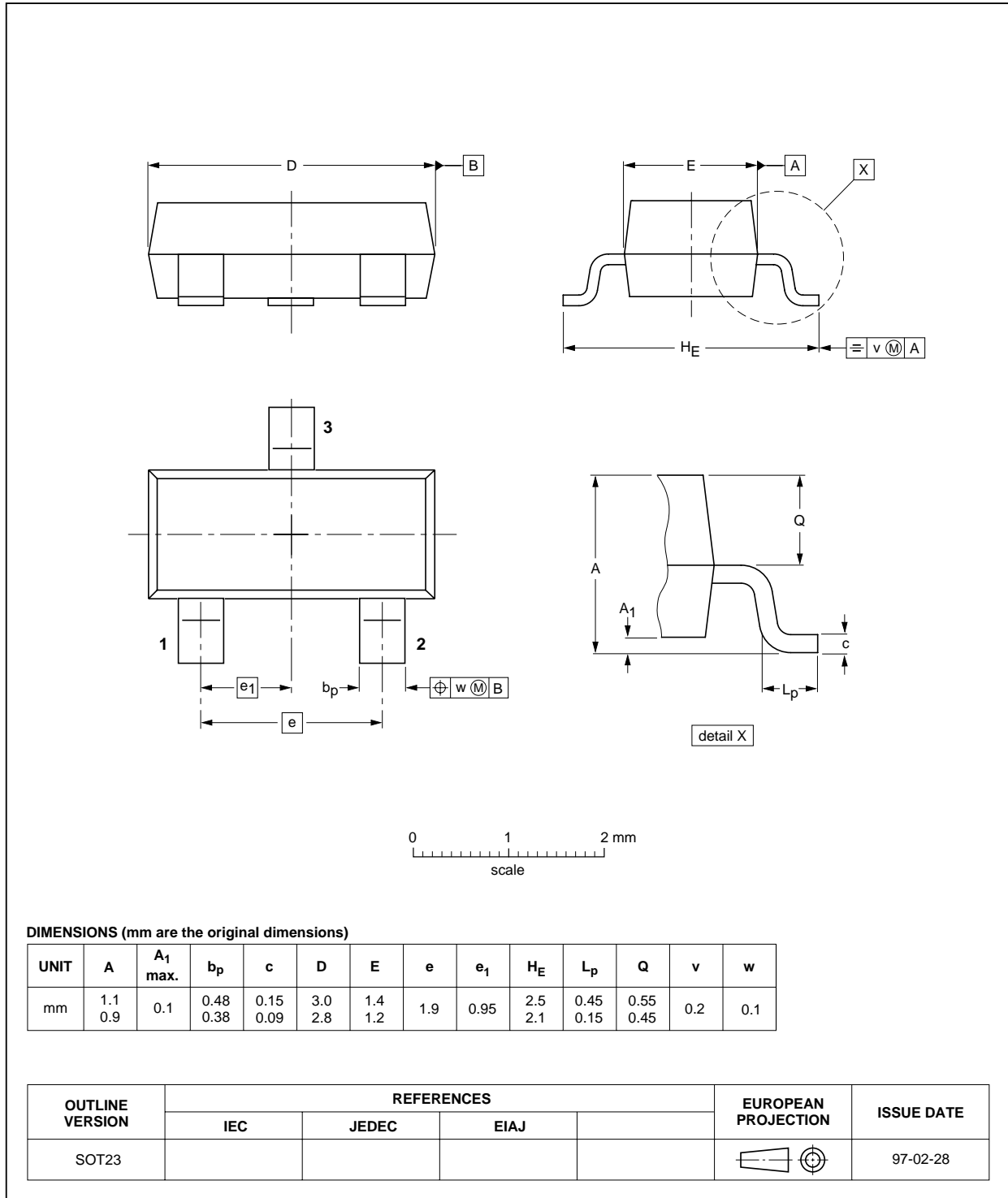
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



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**DEFINITIONS**

| <b>Data sheet status</b>  |  |
|---|--|
| Objective specification   | This data sheet contains target or goal specifications for product development.  |
| Preliminary specification   | This data sheet contains preliminary data; supplementary data may be published later.  |
| Product specification   | This data sheet contains final product specifications.   |
| Short-form specification  | The data in this specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook. |
| <b>Limiting values</b>  |  |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability. |  |
| <b>Application information</b>  |  |
| Where application information is given, it is advisory and does not form part of the specification.   |  |

**LIFE SUPPORT APPLICATIONS**

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